



Listing and specification of **processing** equipment at ISC Konstanz

30.05.2016

Processing equipment		
apparatus	applications	properties
<p>inline wet-bench (RENA)</p>	<ul style="list-style-type: none"> - wafer cleaning - isotexture - P-glass etch - edge isolation - single side isotexture - single side polishing - emitter etch back 	<ul style="list-style-type: none"> - 3 tracks - format: 80 x 120 mm² to 210 x 210 mm² - up to 2.5m/s - temperature control: 3°C-98°C - 150l fluid storage
<p>batch wet-bench (RENA)</p>	<ul style="list-style-type: none"> - alkaline texture - KOH + RENA monoTEX texture - HF/O₃ wafer cleaning - KOH/H₂O₂-cleaning - HF/HCl-cleaning - HF/O₃ emitter etch back 	<ul style="list-style-type: none"> - semi-automatic - wafer-format: 125 mm² or 156 mm² - 50 wafers per batch
<p>indus batch wet-bench (RENA)</p>	<ul style="list-style-type: none"> - alkaline etching - industrial cleaning - piranha cleaning - drying 	<ul style="list-style-type: none"> - format: 50 x 50 mm² to 210 x 210 mm² - alkaline bath with heating - HCl bath - HF bath - different deionised water cascades for rinsing - piranha bath - oven for drying
<p>diffusion furnace (centrotherm)</p>	<ul style="list-style-type: none"> - POCl₃ diffusion - BBr₃ diffusion - LP POCl diffusion (single or half pitch loading) - LP BBr₃ diffusion (single or half pitch loading) 	<ul style="list-style-type: none"> - format: 50 x 50 mm² to 210 x 210 mm² - up to 200 wafers (400 wafers back to back)
<p>PECVD furnace (centrotherm)</p>	<ul style="list-style-type: none"> - PECVD - LPCVD - thermal and wet oxidation - sintering tube 	<ul style="list-style-type: none"> - standard industrial system - wafer format: any size up to 210 x 210 mm² - PECVD gases: SiH₄, NH₃, N₂, H₂, N₂O, SF₆, free line for e.g. doping gas - PECVD graphite boats for up to 196 wafers - LPCVD gases: DCS, NH₃, N₂, H₂ - sintering of contacts under ArH-atmosphere

Processing equipment

apparatus	applications	properties
 <p>screen printer (Baccini)</p>	<ul style="list-style-type: none"> - metallization of front and rear 	<ul style="list-style-type: none"> - semiautomatic screen printer - format: 50 x 50 mm² to 210 x 210 mm² - optical adjustment with four cameras - printing process in less than 10s - edge & fiducial alignment
 <p>Screen printer (Micro-Tec)</p>	<ul style="list-style-type: none"> - Front side metallization 	<ul style="list-style-type: none"> - Semiautomatic screen printer - Wafer format: 125 x 125 or 156 x 156 mm² - Alignment with two freely adjustable cameras - Highly precise fiducial alignment for dual print, double print, print on print or print on laser structure - Printing under N₂ atmosphere possible - Pressure controlled squeegee head for homogeneous print results
 <p>dryer (Baccini)</p>	<ul style="list-style-type: none"> - drying of metallized samples 	<ul style="list-style-type: none"> - semi automatic operation - paternoster drying furnace - format: 50 x 50 mm² to 156 x 156 mm² - 4 heating zones - 250 places - one drying cycle: ca. 10 minutes - temperature up to 230°C
 <p>belt-furnace (centrotherm)</p>	<ul style="list-style-type: none"> - firing of metallized samples 	<ul style="list-style-type: none"> - metal belt furnace - format: 50 x 50 mm² to 210 x 210 mm² - 7 m long - 6 heating zones - up to 1000°C - approx. 1.5 min per process (with std. parameters)
 <p>laser (Rofin)</p>	<ul style="list-style-type: none"> - numbering - cutting - edge isolation - fine lines opening on dielectric layers (application for selective emitter) 	<ul style="list-style-type: none"> - ND: YV04 green laser for class 1 operation - easy touch pad software, automatic door security - wave length: 532nm - frequency: 15-200 kHz - power: 18W - fine lines of 50µm width

Processing equipment

apparatus	applications	properties
 <p>Laser (Rofin)</p>	<ul style="list-style-type: none"> - Ablation of dielectrics - Large area Ablation for ZEBRA 	<ul style="list-style-type: none"> - Nd:YAG laser with SHG module for 532nm - dual rotary table for fast processing - 156x156mm² wafer - frequency: 6-50kHz - pulse width: 120 ns @ 10 kHz - power: 100W - rectangular spot with 300x600µm - 8-point automatic wafer alignment
 <p>Laser (Rofin)</p>	<ul style="list-style-type: none"> - numbering - cutting - edge isolation - cell repair (isolate shunts) 	<ul style="list-style-type: none"> - diode pumped fiber laser (Yb) with 1064 nm - single cell processing (50x50 – 156x156 mm²) - frequency: 20-100 kHz - pulse width: 100 ns @ 20 kHz - power: 14 W - spot size: 40-60 µm
 <p>Laser edge isolation</p>	<ul style="list-style-type: none"> - laser edge isolation - semi automatic - industrial application 	<ul style="list-style-type: none"> - diode pumped Nd:YAG laser with 1064 nm - semi automatic cell processing (125x125 – 156x156 mm²) - frequency: 6-65 kHz - power: 100 W - spot size: 60 µm - 400 wafer/hr (semi-automatic) - 1440 wafer/hr (in automisation)
 <p>stringer</p>	<ul style="list-style-type: none"> - Soldering of ribbons to the solar cells. - Stringing of solar cells 	<ul style="list-style-type: none"> - Three step process with manageable properties - Heat up, soldering, cool down temperatures and time lapse tuneable - Cell holders on/off selectable - Infrared heating - Designed for 6" cells with 2 and 3 busbars - String length variable
 <p>Laminator</p>	<ul style="list-style-type: none"> - Module lamination 	<ul style="list-style-type: none"> - lamination of mini-modules (1 cell) up to 60 cell modules: glass-foil and glass-glass - classical lamella laminator with pins - lamella pressure adaptable vial control of vacuum level in upper chamber - top lamella up to 80 °C - hot plate up to 180 °C - free design of lamination recipe - log of temperature + pressure profile possible

Processing equipment

apparatus

applications

properties



climatic chamber

- Environmental testing of solar module samples
- Damp heat testing
- Humidity freeze testing
- Thermo-cycling

- Chamber size for up to 160 one-cell mini modules or 30 two-cell modules
- Climatic testing recipe with option to program temperature and humidity ramps
- Full humidity control (up to 100% humidity) and temperature control (-40 degrees Celsius up to 90 degrees Celsius)
- Access from outside to testing chamber allows for example measurement of contact resistances or application of current to modules during test

several fume hoods



- preparation of samples

- with or without gas-washer



Muffle furnace

- Curing of ECA
- General high T processes

- Up to 3000°C
- Definition of heat ramp
- Definition of time at plateau
- Metals in chamber allowed

spinner

- thin surface coatings




process gases

- 12 process gases

- N₂, H₂, O₂ (technical and high purity)
- C₃H₈
- Ar, N₂O, SF₆
- SiH₂Cl₂, CH₄, SiH₄, NH₃

Processing equipment

apparatus	applications	properties
 <p>chemicals</p>	- >10 different chemicals	<ul style="list-style-type: none">- HCl (32%) (hydrochloric acid)- HF (50%) (hydrofluoric acid)- H₂O₂ (30%) (hydrogen peroxide)- NaOH (pellets) (sodium hydroxide)- KOH (potassium hydroxide)- HNO₃ (65%) (nitric acid)- CH₃COOH (99.8%) (acetic acid)- H₂SO₄ (95-97%) (sulphuric acid)- Na₂CO₃ (sodium carbonate)- H₃PO₄ (ortho-phosphorus acid)- 2-propanol (IPA)

